

Amendment Under 37 C.F.R. § 1.111  
U.S. Appl. No. 09/881,782

*Consolidated  
A1*

~~crystal layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer a pad electrode for wide bonding is on the center of the upper surface of said window layer, and said second conduction-type surface ohmic electrode is composed of a plurality of electrodes.~~

*E1  
A2*

4. (Amended) The group-III nitride semiconductor light-emitting diode as claimed in claim 1 or 2, wherein said second conduction-type surface ohmic electrodes are disposed at isometric positions from the center of said pad electrode.

*sub C3  
A3*

11. (Amended) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure, and a window layer comprising an electrically conducting transparent oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer a pad electrode for wire bonding is on the center of the upper surface of said window layer, and said surface ohmic electrode is composed of a plurality of electrodes.

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A4E1  
14. (Amended) The electrode for group-III nitride semiconductor light-emitting diodes as claimed in claim 11 or 12, wherein said surface ohmic electrodes are disposed at isometric positions from the center of said pad electrode.

sub C5  
A5  
19. (Amended) A method for producing an electrode for group-III nitride semiconductor light-emitting diodes, comprising  
forming a plurality of surface ohmic electrodes in contact with a surface of a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure,  
then covering the surface of said group-III nitride crystal layer and said surface ohmic electrodes to form a window layer comprising an electrically conducting transparent oxide crystal layer conductive with said surface ohmic electrodes, and  
then forming a pad electrode for wire bonding on a center of the upper surface of said window layer conductive with said window layer.

Please add new claims 21 and 22 as follows:

sub B1  
A6  
21. (New) A group-III nitride semiconductor light-emitting diode comprising at least a first conduction-type single crystal substrate provided with a first conduction-type back-surface ohmic electrode on a back surface thereof, a buffer layer comprising a boron phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure on said buffer layer, and a window layer comprising an electrically conducting transparent oxide crystal layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface

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*Cancelled  
B1  
Cancelled  
A4*

ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer disposed in an open light-emitting region other than a projective region of the pad electrode surface of said group-III nitride crystal layer and a pad electrode for wire bonding is on the center of the upper surface of said window layer and wherein a sum of areas of said second conduction-type surface ohmic electrodes is from 5 to 30% of a total area of said open light-emitting region.

22. (New) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure, and a window layer comprising an electrically conducting transparent oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer in an open light-emitting region other than a projective region of a pad electrode on the surface of said group-III nitride crystal layer and comes into contact with the surface of said group-III nitride crystal layer and said pad electrode for wire bonding is on the center of the upper surface of said window layer, wherein a sum of said surface ohmic electrodes is from 5 to 30% of a total area of the open light-emitting region.

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